Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listings of Claims:

- 1. (canceled)
- (currently amended) A The composition of Claim 1, comprising:

 a first component that exhibits a predetermined change in response to

 radiation; and

a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to form an inhomogeneous material having physical properties substantially determined by said second component, wherein said second component comprises porous silica particles, and wherein said first component is a minority component of said inhomogeneous material.

(currently amended) A The composition of Claim 1, comprising:

 a first component that exhibits a predetermined change in response to

 radiation; and

a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to form an inhomogeneous material having physical properties substantially determined by said second component, wherein said second component comprises porous silica particles, and wherein said second component is a majority component of said inhomogeneous material.

- 4. (currently amended) A composition comprising:
- a first component that <u>exhibits</u> provides a predetermined <u>change in</u> response to radiation; and

a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to for form an inhomogeneous material having physical properties substantially determined by said second component,

SILICON VALLEY
'ATENT GROUP LLP
50 Mission College Biv
Suite 360
'anta Clara, CA 95054
(408) 982-8200
FAX (408) 982-8210

wherein a ratio of a size of one of said portions of said second component to a size of one of said portions of said first component is greater than about 5.

- 5. (original) The composition of Claim 4, wherein said ratio is greater than about 10.
- 6. (currently amended) The composition of Claim <u>2</u> 1, wherein said radiation includes ultraviolet light.
 - (currently amended) A <u>The</u> composition <u>of Claim 2</u> comprising:

 a first component that provides a predetermined response to radiation; and
 a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component for form an inhomogeneous material having physical properties substantially determined by said second component,

wherein said predetermined <u>change in</u> response to radiation includes dissociation.

- 8. (currently amended) The composition of Claim <u>2</u> 4, wherein said predetermined change <u>in response to radiation</u> includes polymerization.
 - (currently amended) A composition comprising:
 a first component that provides a predetermined response to radiation; and a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to for form an inhomogeneous material having physical properties substantially determined by said second component,

wherein said first component comprises a photosensitive derivative of a polyhedral oligomeric silsesquioxane.

10. (currently amended) A composition comprising:a first component that provides a predetermined response to radiation; anda second component;

SILICON VALLEY
'ATENT GROUP LLP
50 Mission College Blvd
Suite 360
'anta Clara, CA 95054
(408) 982-8200
FAX (408) 982-8210

wherein upon curing of said composition portions of said first component bind together portions of said second component to for form an inhomogeneous material having physical properties substantially determined by said second component,

wherein said first component comprises a methacrylate substituted polyhedral oligomeric silsesquioxane.

- 11. (canceled)
- 12. (currently amended) The composition of Claim $\underline{2}$ 4, wherein said second component comprises silicalite particles.
- 13. (currently amended) The composition of Claim <u>2</u> 4, further comprising a material that responds to light to initiate a polymerization reaction.
- 14. (currently amended) The composition of Claim <u>2</u> 1, wherein said physical properties are macroscopic physical properties.
- 15. (currently amended) The composition of Claim <u>2</u> 4, wherein said macroscopic physical properties include a dielectric constant of said inhomogeneous material.
- 16. (currently amended) The composition of Claim <u>2</u> 4, wherein said inhomogeneous material has a dielectric constant less than about 2.6.

17-31. (canceled)

32. (currently amended) An The integrated circuit of Claim 29 comprising:
a metal layer; and
an insulating layer overlying said metal layer, said insulating layer

comprising:

a first component that exhibits a predetermined change in response to radiation; and

a second component;

wherein upon curing of said composition portions of said first
component bind together portions of said second component to form an
inhomogeneous material having physical properties substantially determined
by said second component, wherein said second component comprises

SILICON VALLEY 'ATENT GROUP I.I.F '90 Mission College Blvd Suite 360 ianta Clara, CA 95054 (408) 982-8200 FAX (408) 982-8210

- <u>porous silica particles, and</u> wherein said predetermined change includes polymerization.
- 33. (currently amended) An The integrated circuit of Claim 29 comprising:

 a metal layer; and
 an insulating layer overlying said metal layer, said insulating layer
 comprising:

a first component that exhibits a predetermined change in response to radiation; and

a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to form an inhomogeneous material having physical properties substantially determined by said second component, wherein said second component comprises porous silica particles, and wherein said first component comprises a photosensitive derivative of a polyhedral oligomeric silsesquioxane.

34. (currently amended) An The integrated circuit of Claim 29 comprising:

a metal layer; and
an insulating layer overlying said metal layer, said insulating layer
comprising:

a first component that exhibits a predetermined change in response to radiation; and

a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to form an inhomogeneous material having physical properties substantially determined by said second component, wherein said second component comprises porous silica particles, and wherein said first component comprises a methacrylate substituted polyhedral oligomeric silsesquioxane.

35. (currently amended) An The integrated circuit of Claim 29 comprising: a metal layer; and

SILICON VALLEY
'ATENT GROUP ILIP

50 Mission College Blvc,
Suite 360
'anna Clara, CA 95054
(408) 982-8200
FAX (408) 982-8210

an insulating layer overlying said metal layer, said insulating layer comprising:

<u>a first component that exhibits a predetermined change in response to radiation; and</u>

a second component;

wherein upon curing of said composition portions of said first component bind together portions of said second component to form an inhomogeneous material having physical properties substantially determined by said second component, wherein said second component comprises porous silica particles, and wherein said second component comprises silicalite particles.

- 36. (currently amended) The integrated circuit of Claim <u>35</u> 29 wherein said metal layer and said insulating layer are part of a dual damascene structure.
- 37. (currently amended) The integrated circuit of Claim <u>35</u> 29 wherein said metal <u>layer comprises</u> is copper.
- 38. (currently amended) The integrated circuit of Claim <u>35</u> 29 comprising a barrier layer between said metal layer and said insulating layer.
- 39. (currently amended) The integrated circuit of Claim 38 wherein said barrier layer comprises a material selected from the group consisting or silicon nitride, silicon oxynitride and silicon carbide.
- 40. (currently amended) The integrated circuit of Claim <u>35</u> 29 wherein said insulating layer has a dielectric constant in range of about 2.2 to about 2.6.

SILICON VALLEY

50 Mission College Blvd Suite 360 ianta Clara, CA 95054 (408) 982-8200 FAX (408) 982-8210